Roll No.

Total Pages: 3

322103

December, 2019 M.Tech. (VLSI) 1st SEMESTER VLSI Technology with MEMS Applications (MVLE106)

Time: 3 Hours]

[Max. Marks: 75

Instructions:

- 1. It is compulsory to answer all the questions (1.5 marks each) of Part-A in short.
- 2. Answer any four questions from Part-B in detail.
- 3. Different sub-parts of a question are to be attempted adjacent to each other.

PART - A

- (a) Give the advantages and applications of SOI structures. (1.5)
 - (b) Why rate of growth in wet oxidation is more compared with the dry oxidation? (1.5)
 - (c) Compare diffusion and ion implantation process. (1.5)
 - d) What is isotropic and anisotropic etching? Discuss.

(1.5)

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	(e)	What is the role of plasma in etching? Discuss.	(1.5)		5.	(a)	Discuss the role of etching process in VLSI fabrication.
	(f)	What is SUPREM and its use in VLSI fabrica	tion?				Explain the process of reactive ion etching. (7.5)
			(1.5)			(b)	Discuss reliability issues in the VLSI technology.
	(g)	What are MEMS? Give some applicatio	ns of				(7.5)
		MEMS.	(1.5)				
	(h)	What is SQUID magnetometer? Discuss.	(1.5)		6.	(a)	What is Bulk and Surface Micromachining? Compare
	(i)	What is wafer bonding? Discuss.	(1.5)				these techniques. (7.5)
	(j)	What are negative and positive photo resists?	(1.5)			(b)	Write short note on finite element method. (7.5)
		PART - B			7.	(a)	What are optical sensors? Discuss operation and give
2.	(a)	Explain the basic transport processes and re-				. ,	their application. (7.5)
		kinetics in vapors phase epitaxy.	(7.5)			(b)	Write a short note on MEMS accelerometer. (7.5)
	(b)	Explain the process of single crystal formatio				` /	
		help of CZ process.	(7.5)				
3.	(a)	Discuss and explain the silicon oxidation model	. (7.5)				
	(b)	Explain the process of molecular beam epitax	y with	~ Y			
		relevant diagram.	(7.5)				
4.	(a)	Describe the different printing techniques u	sed in				
		photolithography process.	(7.5)				
	(b	What is electron beam lithography process? E	xplain.				
		Discuss its advantages over optical lithography.					
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